

NCE N-Channel Enhancement Mode Power MOSFET

Description

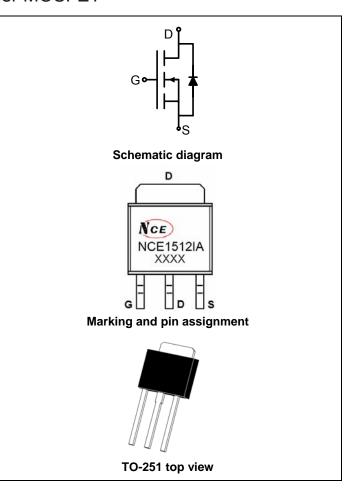
The NCE1512IA uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} = 150V, I_{D} =12A $R_{DS(ON)}$ <160mΩ @ V_{GS} =10V (Typ:130mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE1512IA	NCE1512IA	TO-251	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	12	Α
Drain Current-Pulsed (Note 1)	I _{DM}	50	Α
Maximum Power Dissipation	P _D	55	W
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{θJC}	2.7	°C/W
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Electrical Characteristics (T_C=25 [°]C unless otherwise noted)

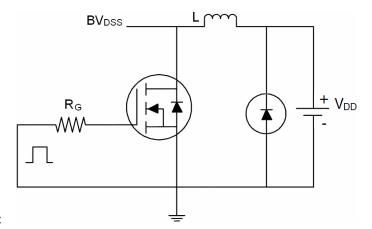
Parameter	Symbol	Condition	Min	Тур	Max	Unit		
Off Characteristics								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	-	-	V		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA		
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA		
On Characteristics (Note 3)								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.5	2	2.5	V		
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A	-	130	160	mΩ		
Forward Transconductance	g FS	V _{DS} =15V,I _D =10A	-	15	-	S		
Dynamic Characteristics (Note4)								
Input Capacitance	C _{lss})/ OF)/)/ O)/	-	900	-	PF		
Output Capacitance	C _{oss}	V_{DS} =25V, V_{GS} =0V, F=1.0MHz	-	115	-	PF		
Reverse Transfer Capacitance	C _{rss}	F=1.UIVITZ	-	70	-	PF		
Switching Characteristics (Note 4)								
Turn-on Delay Time	t _{d(on)}		-	8	-	nS		
Turn-on Rise Time	t _r	V_{DD} =75 V , I_D =1 A , R_L =75 Ω	-	10	-	nS		
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =6 Ω	-	20	-	nS		
Turn-Off Fall Time	t _f	1	-	15	-	nS		
Total Gate Charge	Qg	\/ 75\/ L 4.5A	-	19		nC		
Gate-Source Charge	Q _{gs}	V _{DS} =75V,I _D =1.5A,	-	5.5	-	nC		
Gate-Drain Charge	Q_{gd}	- V _{GS} =10V	-	7	-	nC		
Drain-Source Diode Characteristics								
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =2A	-	-	1.2	V		
Diode Forward Current (Note 2)	Is		-	-	12	Α		

Notes:

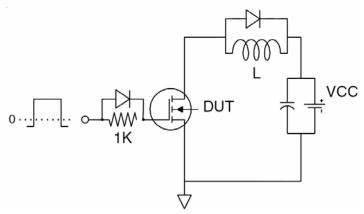
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to product

Test Circuit

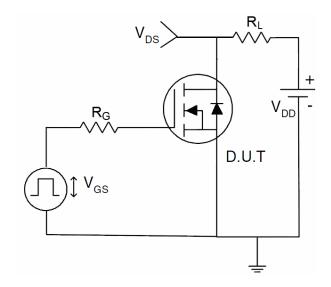
1) E_{AS} Test Circuit



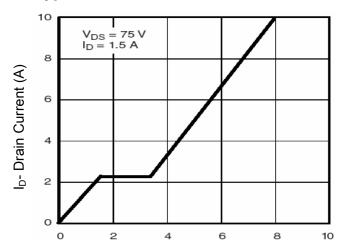
2) Gate Charge Test Circuit



3) Switch Time Test Circuit

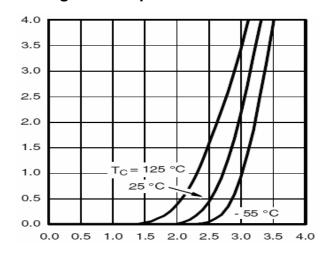


Typical Electrical and Thermal Characteristics (Curves)



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



ID- Drain Current (A)

Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

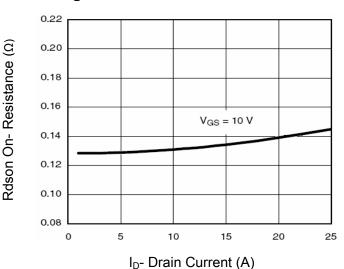


Figure 3 Rdson- Drain Current

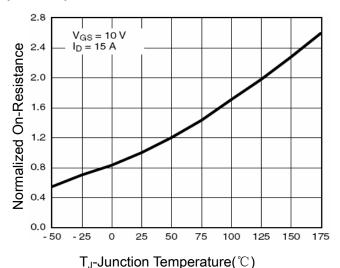


Figure 4 Rdson- Junction Temperature

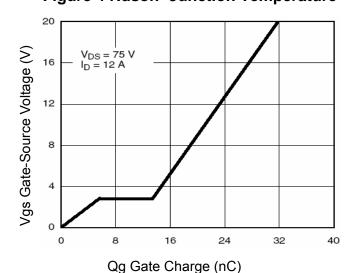


Figure 5 Gate Charge

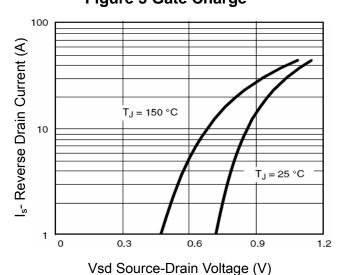


Figure 6 Source- Drain Diode Forward

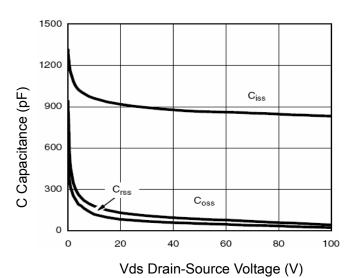


Figure 7 Capacitance vs Vds

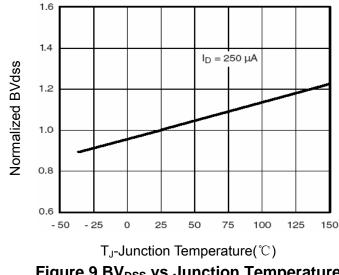


Figure 9 BV_{DSS} vs Junction Temperature

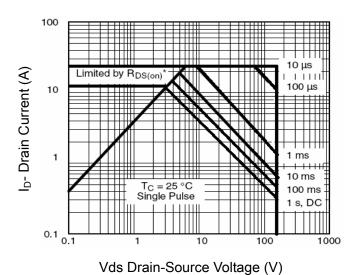
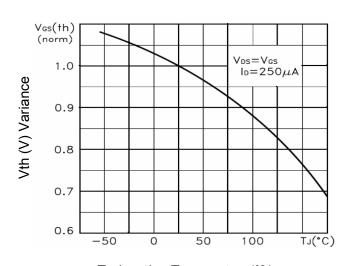


Figure 8 Safe Operation Area



 T_J -Junction Temperature($^{\circ}$ C)



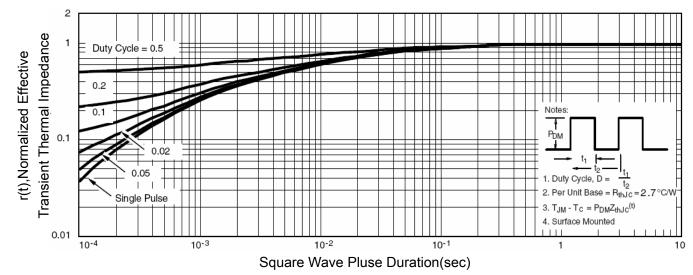
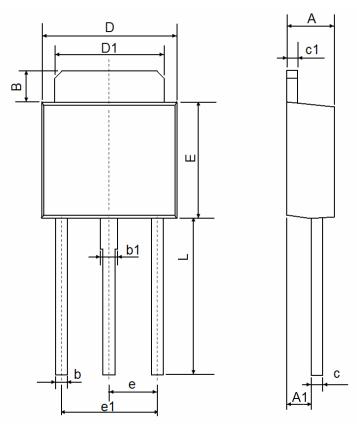


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-251 Package Information



Cumbal	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	1.050	1.350	0.042	0.054	
В	1.350	1.650	0.053	0.065	
b	0.500	0.700	0.020	0.028	
b1	0.700	0.900	0.028	0.035	
С	0.430	0.580	0.017	0.023	
c1	0.430	0.580	0.017	0.023	
D	6.350	6.650	0.250	0.262	
D1	5.200	5.400	0.205	0.213	
Е	5.400	5.700	0.213	0.224	
е	2.300	2.300 TYP 0.091 TY		TYP	
e1	4.500	4.700	0.177	0.185	
L	7.500	7.900	0.295	0.311	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$

Pb-Free Product

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